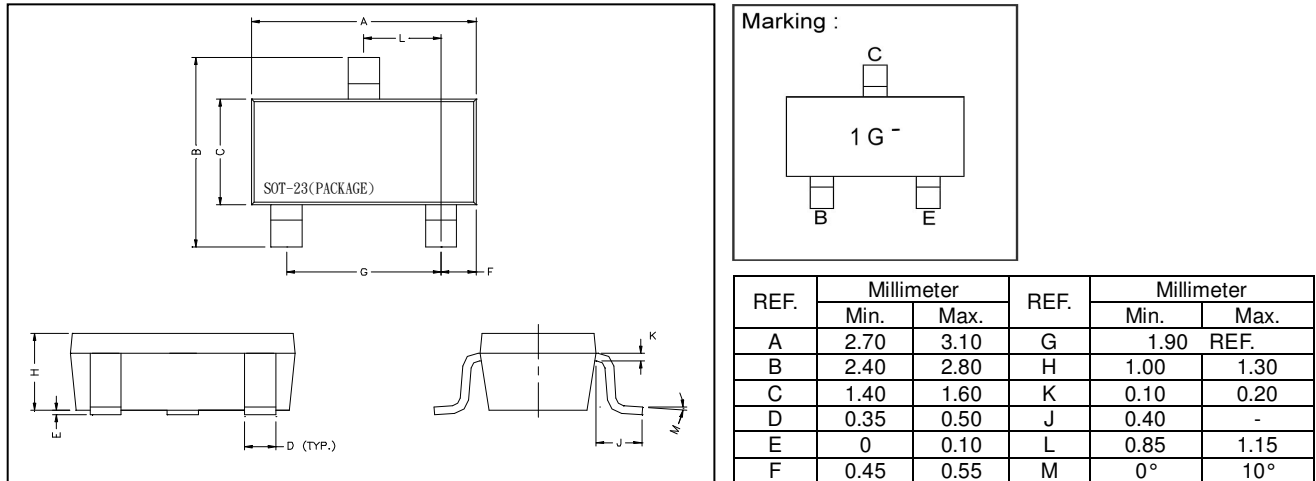


GMBTA06NPN SILICON TRANSISTOR

Description

The GMBTA06 is designed for general purpose amplifier applications.

Package Dimensions



Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Ratings	Unit
Junction Temperature	T _j	+150	°C
Storage Temperature	T _{stg}	-55~+150	°C
Collector to Base Voltage	V _{CB0}	80	V
Collector to Emitter Voltage	V _{CEO}	80	V
Emitter to Base Voltage	V _{EB0}	4	V
Collector Current	I _c	500	mA
Total Power Dissipation(Note1)	P _D	350	mW

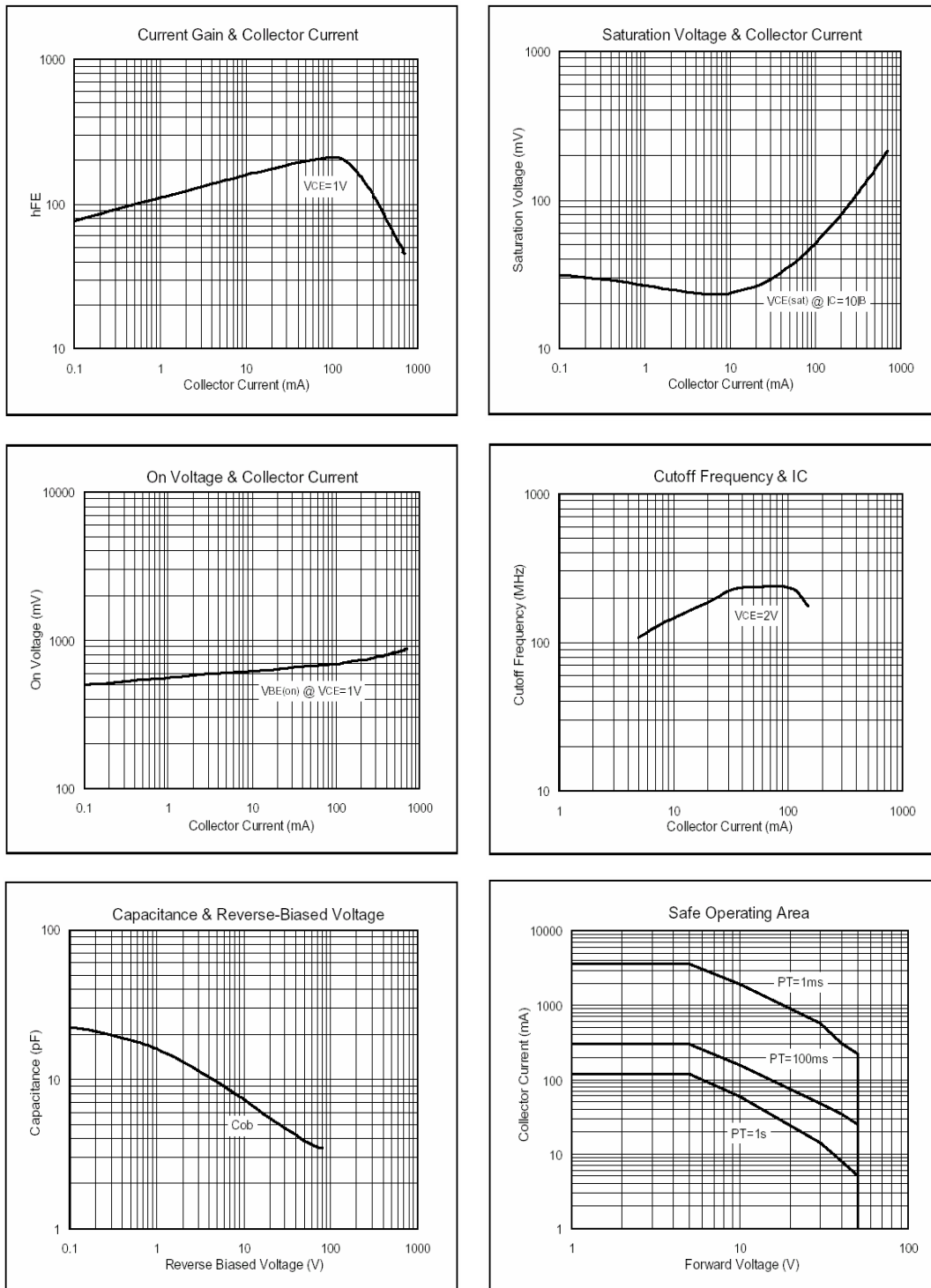
Note 1. Device mounted on FR-4=1.6*1.6*0.06in

Electrical Characteristics(Ta = 25°C ,unless otherwise noted)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BV _{CB0}	80	-	-	V	I _c =100uA, I _E =0
BV _{CEO}	80	-	-	V	I _c =1mA, I _B =0
BV _{EB0}	4	-	-	V	I _E =100uA, I _c =0
I _{CB0}	-	-	100	nA	V _{CB} =80V, I _E =0
I _{CEO}	-	-	100	nA	V _{CE} =80V, I _B =0
*V _{CE(sat)}	-	-	250	mV	I _c =100mA, I _B =10mA
*V _{BE(on)}	-	-	1.2	V	V _{CE} =1V, I _c =100mA
*h _{FE1}	50	-	-		V _{CE} =1V, I _c =10mA
*h _{FE2}	50	-	-		V _{CE} =1V, I _c =100mA
f _T	100	-	-	MHz	V _{CE} =2V, I _c =10mA, f=100MHz

* Pulse Test: Pulse Width ≤ 380μs, Duty Cycle ≤ 2%

Characteristics Curve



Important Notice:

- All rights are reserved. Reproduction in whole or in part is prohibited without the prior written approval of GTM.
- GTM reserves the right to make changes to its products without notice.
- GTM semiconductor products are not warranted to be suitable for use in life-support Applications, or systems.
- GTM assumes no liability for any consequence of customer product design, infringement of patents, or application assistance.

Head Office And Factory:

- **Taiwan:** No. 17-1 Tatung Rd. Fu Kou Hsin-Chu Industrial Park, Hsin-Chu, Taiwan, R. O. C.
- TEL : 886-3-597-7061 FAX : 886-3-597-9220, 597-0785
- **China:** (201203) No.255, Jang-Jiang Tsai-Lueng RD. , Pu-Dung-Hsin District, Shang-Hai City, China
- TEL : 86-21-5895-7671 ~ 4 FAX : 86-21-38950165